

30th RD50 Workshop (Krakow)

Wednesday 7 June 2017

Defect and Material Engineering (13:20 - 15:30)

-Conveners: Michael Moll

time	[id] title	presenter
13:20	[28] Determination of the p-spray profile for n ⁺ p silicon sensors using a MOSFET	FRETWURST, Eckhart
13:40	[7] Anneal induced transforms of radiation defects in hadron and electron irradiated Si	Ms MESKAUSKAITE, Dovile
14:00	[9] Effect of nitrogen doping on characteristics of pad detectors irradiated with high proton fluences	Prof. KAMIŃSKI, Paweł
14:20	[2] Measurement of the acceptor removal rate in silicon pad diodes	Mr DIAS DE ALMEIDA, Pedro Goncalo
14:40	[48] Update on the RD50 project NitroStrip	BASELGA BACARDIT, Marta
15:00	[46] Discussion	MOLL, Michael